

SG40SC10U

100V 40A

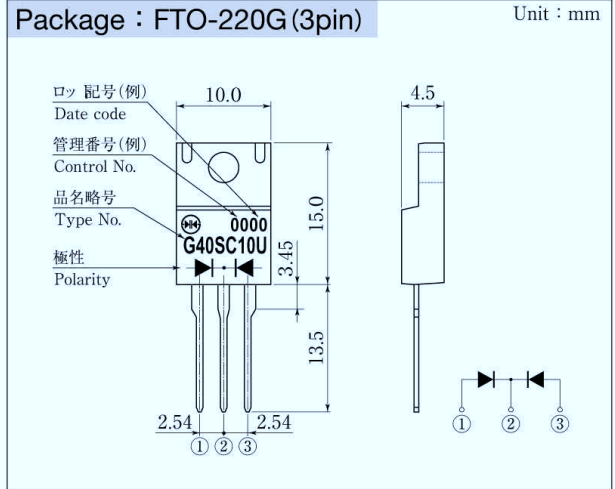
特長

- 低 V_F
- 低 I_R
- 高耐圧
- 高速リカバリ損失低減

Feature

- Low V_F
- Low I_R
- High Voltage
- High temperature recovery loss reduction

■外観図 OUTLINE



外形図については新電元 Web サイトをご参照下さい。捺印表示については捺印仕様をご確認下さい。

For details of the outline dimensions, refer to our web site. As for the marking, refer to the specification "Marking, Terminal Connection".

■定格表 RATINGS

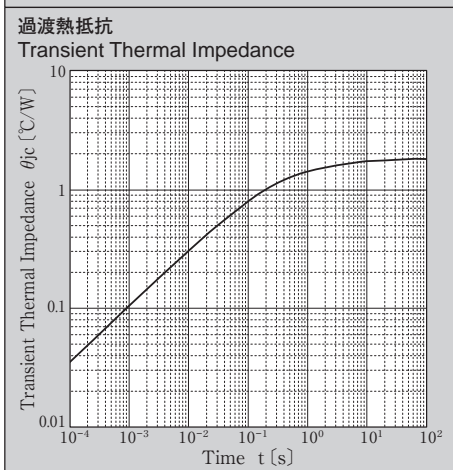
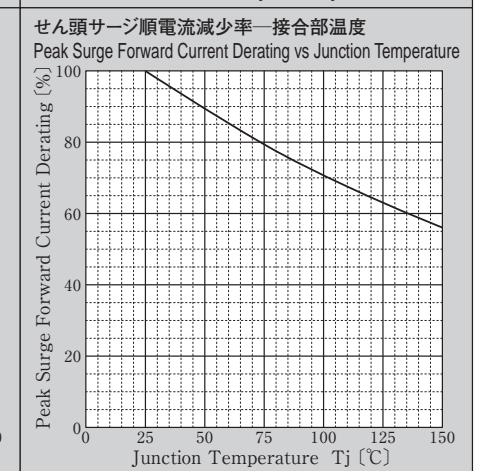
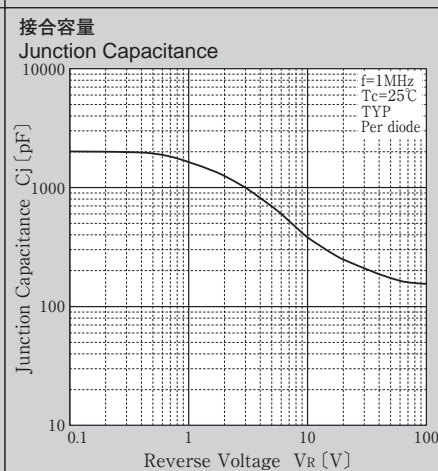
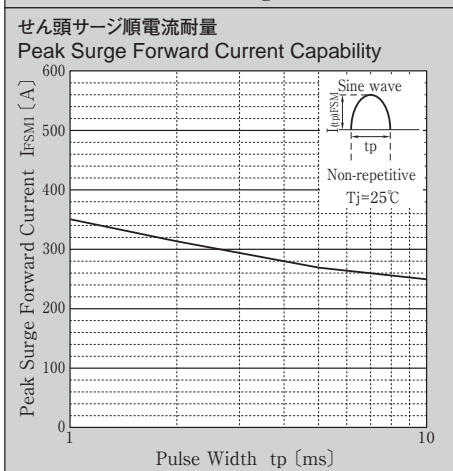
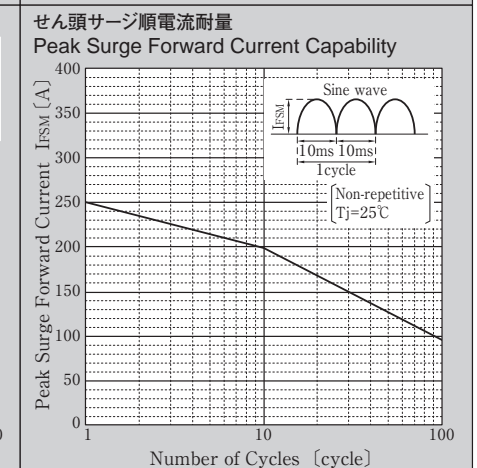
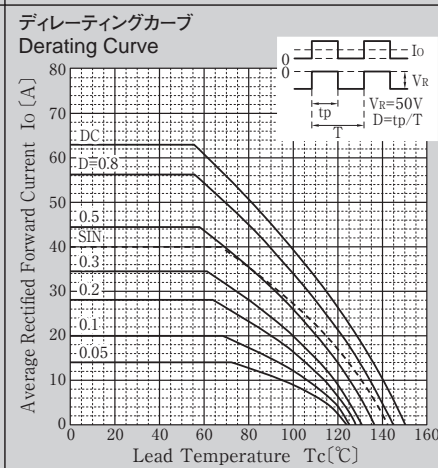
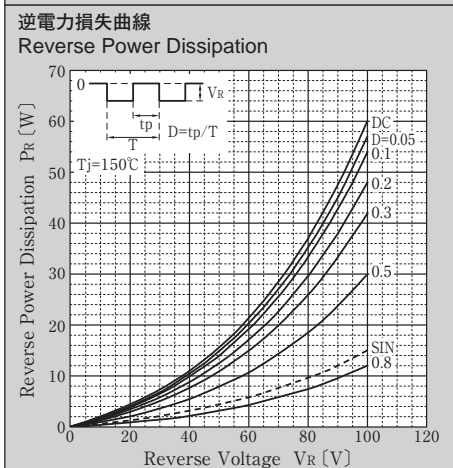
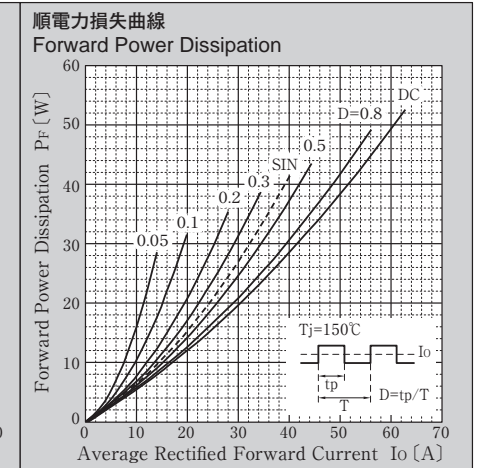
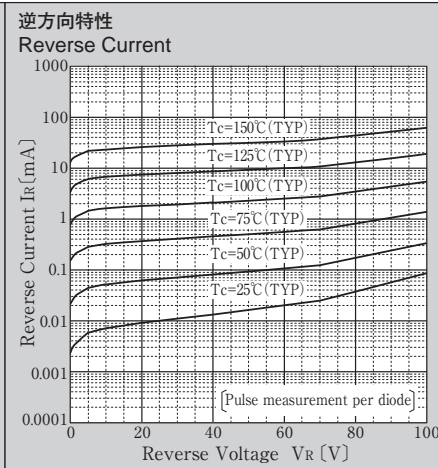
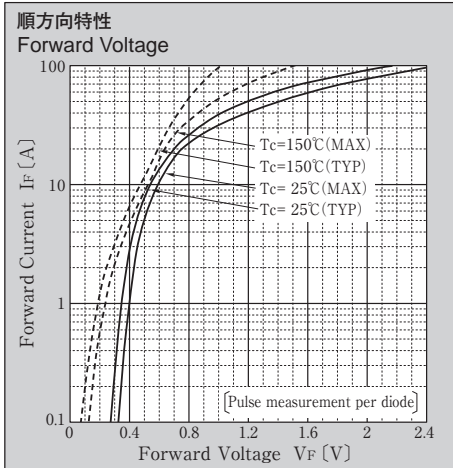
●絶対最大定格 Absolute Maximum Ratings (指定のない場合は $T_c = 25^\circ\text{C}$ / unless otherwise specified)

項目 Item	記号 Symbol	条件 Conditions	規格値 Ratings	単位 Unit
保存温度 Storage Temperature	T_{stg}		- 55 ~ 150	$^\circ\text{C}$
接合部温度 Operating Junction Temperature	T_j		150	$^\circ\text{C}$
せん頭逆電圧 Maximum Reverse Voltage	V_{RM}		100	V
出力電流 Average Rectified Forward Current	I_o	50Hz 正弦波, 抵抗負荷, 一素子当りの出力電流平均値 $I_o/2$, $T_c = 93^\circ\text{C}$ 50Hz sine wave, Resistance load, Rating for each diode $I_o/2$, $T_c = 93^\circ\text{C}$	30	A
		50Hz 正弦波, 抵抗負荷, 一素子当りの出力電流平均値 $I_o/2$, $T_c = 67^\circ\text{C}$ 50Hz sine wave, Resistance load, Rating for each diode $I_o/2$, $T_c = 67^\circ\text{C}$	40	
せん頭サージ順電流 Peak Surge Forward Current	I_{FSM}	50Hz 正弦波, 非繰り返し 1 サイクルせん頭値, $T_j = 25^\circ\text{C}$ 50Hz sine wave, Non-repetitive 1 cycle peak value, $T_j = 25^\circ\text{C}$	250	A
	I_{FSM1}	$t_p = 1\text{ms}$ 正弦波, 非繰り返し 1 サイクルせん頭値, $T_j = 25^\circ\text{C}$ $t_p = 1\text{ms}$ Sine wave, Non-repetitive 1 cycle peak value, $T_j = 25^\circ\text{C}$	350	
絶縁耐圧 Dielectric Strength	V_{dis}	一括端子・ケース裏面間, AC 1 分間印加 Terminals to case backside, AC 1 minute	1.5	kV
締め付けトルク Mounting Torque	TOR	(推奨値: $0.3\text{N}\cdot\text{m}$) (Recommended torque: $0.3\text{N}\cdot\text{m}$)	0.5	$\text{N}\cdot\text{m}$

●電氣的・熱的特性 Electrical Characteristics (指定のない場合は $T_c = 25^\circ\text{C}$ / unless otherwise specified)

順電圧 Forward Voltage	V_F	$I_F = 5\text{A}$,	パルス測定, 一素子当りの規格値 Pulse measurement, Per diode	TYP 0.46 MAX 0.51	V
	V_F	$I_F = 15\text{A}$,	パルス測定, 一素子当りの規格値 Pulse measurement, Per diode	TYP 0.62 MAX 0.68	V
	V_F	$I_F = 20\text{A}$,	パルス測定, 一素子当りの規格値 Pulse measurement, Per diode	TYP 0.69 MAX 0.75	V
逆電流 Reverse Current	I_R	$V_R = 100\text{V}$,	パルス測定, 一素子当りの規格値 Pulse measurement, Per diode	MAX 1	mA
接合容量 Junction Capacitance	C_j	$f = 1\text{MHz}$, $V_R = 50\text{V}$	一素子当りの規格値 Per diode	TYP 170	pF
熱抵抗 Thermal Resistance	θ_{jc}	接合部・ケース間 Junction to case		MAX 1.8	$^\circ\text{C}/\text{W}$

■特性図 CHARACTERISTIC DIAGRAMS



* Sine wave は 50Hz で測定しています。
* 50Hz sine wave is used for measurements.